Eva Monroy

List of Publications by Year
in descending order

386 papers	10,548 citations	38742 50 h-index	49909 87 g-index
388 all docs	388 docs citations	388 times ranked	6859 citing authors

#	Article	IF	Citations
1	Wide-bandgap semiconductor ultraviolet photodetectors. Semiconductor Science and Technology, 2003, 18, R33-R51.	2.0	1,196
2	The effect of the III/V ratio and substrate temperature on the morphology and properties of GaN- and AlN-layers grown by molecular beam epitaxy on Si(1 1 1). Journal of Crystal Growth, 1998, 183, 23-30.	1.5	303
3	Systematic experimental and theoretical investigation of intersubband absorption inGaNâˆ•AlNquantum wells. Physical Review B, 2006, 73, .	3.2	239
4	III nitrides and UV detection. Journal of Physics Condensed Matter, 2001, 13, 7115-7137.	1.8	229
5	High-performance GaN p-n junction photodetectors for solar ultraviolet applications. Semiconductor Science and Technology, 1998, 13, 1042-1046.	2.0	205
6	High-speed, low-noise metalâ€“semiconductorâ€“metal ultraviolet photodetectors based on GaN. Applied Physics Letters, 1999, 74, 762-764.	3.3	175
7	Photoconductive gain modelling of GaN photodetectors. Semiconductor Science and Technology, 1998, 13, 563-568.	2.0	167
8	GaN/AlN short-period superlattices for intersubband optoelectronics: A systematic study of their epitaxial growth, design, and performance. Journal of Applied Physics, 2008, 104, 093501.	2.5	165
9	Photoconductor gain mechanisms in GaN ultraviolet detectors. Applied Physics Letters, 1997, 71, 870-872.	3.3	163
10	III-nitride semiconductors for intersubband optoelectronics: a review. Semiconductor Science and Technology, 2013, 28, 074022.	2.0	159
11	AlGaN-based UV photodetectors. Journal of Crystal Growth, 2001, 230, 537-543.	1.5	153
12	High-quality visible-blind AlGaN p-i-n photodiodes. Applied Physics Letters, 1999, 74, 1171-1173.	3.3	145
13	Room-Temperature Photodetection Dynamics of Single GaN Nanowires. Nano Letters, 2012, 12, 172-176.	9.1	139
14	AlGaN metalâ€“semiconductorâ€“metal photodiodes. Applied Physics Letters, 1999, 74, 3401-3403.	3.3	126
15	Wet etching of GaN grown by molecular beam epitaxy on Si(111). Semiconductor Science and Technology, 2000, 15, 996-1000.	2.0	120
16	Near infrared quantum cascade detector in GaNâˆ•AlGaNâˆ•AlN heterostructures. Applied Physics Letters, 2008, 92, .	3.3	116
17	Intrinsic ferromagnetism in wurtzite (Ga,Mn)N semiconductor. Physical Review B, 2006, 74, .	3.2	107
18	Structure of GaN quantum dots grown under â€œmodified Stranskiâ€“Krastanowâ€• conditions on AlN. Journal of Applied Physics, 2003, 94, 2254-2261.	2.5	102

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19	Analysis and modeling of AlxGa1â^'xN-based Schottky barrier photodiodes. Journal of Applied Physics, 2000, 88, 2081-2091.	2.5	97
20	Metalorganic vapor-phase epitaxy-grown AlGaN materials for visible-blind ultraviolet photodetector applications. Journal of Applied Physics, 1999, 86, 5286-5292.	2.5	92
21	Terahertz intersubband absorption in GaN/AlGaN step quantum wells. Applied Physics Letters, 2010, 97, .	3.3	87
22	Assessment of GaN metalâ€"semiconductorâ€"metal photodiodes for high-energy ultraviolet photodetection. Applied Physics Letters, 2002, 80, 3198-3200.	3.3	86
23	Intersubband spectroscopy of doped and undoped GaN/AlN quantum wells grown by molecular-beam epitaxy. Applied Physics Letters, 2003, 83, 5196-5198.	3.3	85
24	GaN/AlGaN intersubband optoelectronic devices. New Journal of Physics, 2009, 11, 125023.	2.9	84
25	Surfactant effect of In for AlGaN growth by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2003, 93, 1550-1556.	2.5	77
26	Si-doped GaNâˆ•AlN quantum dot superlattices for optoelectronics at telecommunication wavelengths. Journal of Applied Physics, 2006, 100, 044326.	2.5	77
27	AlxGa1â^'xN:Si Schottky barrier photodiodes with fast response and high detectivity. Applied Physics Letters, 1998, 73, 2146-2148.	3.3	73
28	Correlation of Polarity and Crystal Structure with Optoelectronic and Transport Properties of GaN/AlN/GaN Nanowire Sensors. Nano Letters, 2012, 12, 5691-5696.	9.1	73
29	Room temperature demonstration of GaNâˆ•AlN quantum dot intraband infrared photodetector at fiber-optics communication wavelength. Applied Physics Letters, 2006, 88, 143101.	3.3	71
30	Quantum Transport in GaN/AlN Double-Barrier Heterostructure Nanowires. Nano Letters, 2010, 10, 3545-3550.	9.1	71
31	Strain distribution in GaNâˆ•AlN quantum-dot superlattices. Applied Physics Letters, 2005, 87, 203112.	3.3	70
32	Wide bandgap UV photodetectors: a short review of devices and applications. , 2007, , .		68
33	Plastic strain relaxation of nitride heterostructures. Journal of Applied Physics, 2004, 95, 1127-1133.	2.5	66
34	Nanoindentation on AlGaN thin films. Journal of Applied Physics, 1999, 86, 6773-6778.	2.5	65
35	Growth kinetics of N-face polarity GaN by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2004, 84, 3684-3686.	3.3	65
36	Engineering of an insulating buffer and use of AlN interlayers: two optimisations for AlGaNâ€"GaN HEMT-like structures. Physica Status Solidi A, 2003, 195, 93-100.	1.7	64

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37	Internal quantum efficiency of III-nitride quantum dot superlattices grown by plasma-assisted molecular-beam epitaxy. Journal of Applied Physics, 2011, 109, 103501.	2.5	63
38	Growth kinetics and morphology of high quality AlN grown on Si(111) by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 1997, 82, 4681-4683.	2.5	62
39	Molecular-beam epitaxial growth and characterization of quaternary IIIâ€“nitride compounds. Journal of Applied Physics, 2003, 94, 3121-3127.	2.5	60
40	High-quality AlNâˆ•GaN-superlattice structures for the fabrication of narrow-band 1.4â€‰Î¼m photovoltaic intersubband detectors. Applied Physics Letters, 2006, 88, 121112.	3.3	60
41	Effect of the quantum well thickness on the performance of InGaN photovoltaic cells. Applied Physics Letters, 2014, 105, .	3.3	60
42	Influence of AlN overgrowth on structural properties of GaN quantum wells and quantum dots grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2004, 96, 1104-1110.	2.5	57
43	Identification of IIIâ€“N nanowire growth kinetics via a marker technique. Nanotechnology, 2010, 21, 295605.	2.6	57
44	Short wavelength (Î»=2.13Î¼m) intersubband luminescence from GaNâˆ•AlN quantum wells at room temperature. Applied Physics Letters, 2007, 90, 121106.	3.3	56
45	Plasma-assisted molecular-beam epitaxy of AlN(112Â¯2) on m sapphire. Applied Physics Letters, 2007, 90, 131909.	3.3	56
46	Strain relaxation in short-period polar GaN/AlN superlattices. Journal of Applied Physics, 2009, 106, 013526.	2.5	56
47	GaN/AlGaN waveguide quantum cascade photodetectors at Î»â€‰â‰ˆâ€‰1.55â€‰Î¼m with enhanced responsivity and âˆ¼40â€‰GHz frequency bandwidth. Applied Physics Letters, 2013, 102, .	3.3	55
48	Short-wavelength intersubband electroabsorption modulation based on electron tunneling between GaNâˆ•AlN coupled quantum wells. Applied Physics Letters, 2007, 90, 223511.	3.3	54
49	UV Photosensing Characteristics of Nanowire-Based GaN/AlN Superlattices. Nano Letters, 2016, 16, 3260-3267.	9.1	53
50	High-speed operation of GaN/AlGaN quantum cascade detectors at Î»â‰ˆ1.55â€,Î¼m. Applied Physics Letters, 2008, 93, .	3.3	52
51	All-dielectric GaN microcavity: Strong coupling and lasing at room temperature. Applied Physics Letters, 2013, 102, 101113.	3.3	52
52	GaN quantum dots doped with Eu. Applied Physics Letters, 2004, 84, 206-208.	3.3	51
53	High-responsivity submicron metal-semiconductor-metal ultraviolet detectors. Applied Physics Letters, 2002, 81, 1902-1904.	3.3	49
54	Vertical transport in group III-nitride heterostructures and application in AlN/GaN resonant tunneling diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2210-2227.	0.8	49

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55	Electron confinement in strongly coupled GaNâˆ•AlN quantum wells. Applied Physics Letters, 2006, 88, 153113.	3.3	48
56	Visible-blindness in photoconductive and photovoltaic AlGaN ultraviolet detectors. Journal of Electronic Materials, 1999, 28, 240-245.	2.2	46
57	Bias-Controlled Spectral Response in GaN/AlN Single-Nanowire Ultraviolet Photodetectors. Nano Letters, 2017, 17, 4231-4239.	9.1	45
58	Midinfrared intersubband absorption in GaN/AlGaN superlattices on Si(111) templates. Applied Physics Letters, 2009, 95, .	3.3	44
59	Design of broadband high-efficiency superconducting-nanowire single photon detectors. Superconductor Science and Technology, 2016, 29, 065016.	3.5	43
60	High visible rejection AlGaN photodetectors on Si(111) substrates. Applied Physics Letters, 2000, 76, 2785-2787.	3.3	42
61	Effect of doping on the mid-infrared intersubband absorption in GaN/AlGaN superlattices grown on Si(111) templates. Applied Physics Letters, 2010, 96, .	3.3	42
62	Si-doped AlxGa1-xN photoconductive detectors. Semiconductor Science and Technology, 1999, 14, 685-689.	2.0	40
63	Thermal stability of Pt- and Ni-based Schottky contacts on GaN and Al0.31Ga0.69N. Semiconductor Science and Technology, 2002, 17, L47-L54.	2.0	40
64	Intersubband Transition-Based Processes and Devices in AlN/GaN-Based Heterostructures. Proceedings of the IEEE, 2010, 98, 1234-1248.	21.3	40
65	Time response analysis of ZnSe-based Schottky barrier photodetectors. Applied Physics Letters, 2000, 77, 2761-2763.	3.3	39
66	AlGaN ultraviolet photodetectors grown by molecular beam epitaxy on Si(111) substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 159-162.	3.5	39
67	GaN-based quantum dot infrared photodetector operating at 1.38â€…[micro sign]m. Electronics Letters, 2005, 41, 1077.	1.0	39
68	Intraband absorption of doped GaNâˆ•AlN quantum dots at telecommunication wavelengths. Applied Physics Letters, 2005, 87, 101912.	3.3	39
69	Suppression of nonradiative processes in long-lived polar GaN/AlN quantum dots. Applied Physics Letters, 2009, 95, 131903.	3.3	39
70	Properties of a hole trap inn-type hexagonal GaN. Journal of Applied Physics, 2002, 91, 2998-3001.	2.5	38
71	Modification of GaN(0001) growth kinetics by Mg doping. Applied Physics Letters, 2004, 84, 2554-2556.	3.3	38
72	Optically nonlinear effects in intersubband transitions of GaNâˆ•AlN-based superlattice structures. Applied Physics Letters, 2007, 91, 131115.	3.3	38

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73	Growth optimization and doping with Si and Be of high quality GaN on Si(111) by molecular beam epitaxy. Journal of Electronic Materials, 1998, 27, 276-281.	2.2	37
74	Diamond UV detectors for future solar physics missions. Diamond and Related Materials, 2001, 10, 673-680.	3.9	37
75	Intersubband resonant enhancement of second-harmonic generation in GaNâˆ•AlN quantum wells. Applied Physics Letters, 2006, 89, 151101.	3.3	37
76	Electrically adjustable intersubband absorption of a GaNâˆ•AlN superlattice grown on a transistorlike structure. Applied Physics Letters, 2006, 89, 101121.	3.3	37
77	Luminescence properties of highly Si-doped AlN. Applied Physics Letters, 2006, 88, 071906.	3.3	36
78	High In-content InGaN layers synthesized by plasma-assisted molecular-beam epitaxy: Growth conditions, strain relaxation, and In incorporation kinetics. Journal of Applied Physics, 2014, 116, .	2.5	36
79	Ge doping of GaN beyond the Mott transition. Journal Physics D: Applied Physics, 2016, 49, 445301.	2.8	36
80	Nanotechnology for SAW devices on AlN epilayers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 154-158.	3.5	34
81	Investigation of the negative differential resistance reproducibility in AlN/GaN double-barrier resonant tunnelling diodes. Applied Physics Letters, 2011, 99, 182109.	3.3	34
82	Alloy inhomogeneity and carrier localization in AlGaN sections and AlGaN/AlN nanodisks in nanowires with 240â€"350â€‰nm emission. Applied Physics Letters, 2014, 105, .	3.3	34
83	GaN-based solar-ultraviolet detection instrument. Applied Optics, 1998, 37, 5058.	2.1	33
84	Comparison of the structural quality in Ga-face and N-face polarity GaN/AlN multiple-quantum-well structures. Semiconductor Science and Technology, 2006, 21, 612-618.	2.0	33
85	Intraband Absorption in Self-Assembled Ge-Doped GaN/AlN Nanowire Heterostructures. Nano Letters, 2014, 14, 1665-1673.	9.1	33
86	Near-Infrared Intersubband Photodetection in GaN/AlN Nanowires. Nano Letters, 2017, 17, 6954-6960.	9.1	33
87	Interband and intersubband optical characterization of semipolar (112Â¯2)-oriented GaN/AlN multiple-quantum-well structures. Applied Physics Letters, 2008, 93, 111906.	3.3	32
88	Femto-second electron transit time characterization in GaN/AlGaN quantum cascade detector at 1.5 micron. Applied Physics Letters, 2011, 99, .	3.3	32
89	In incorporation during the growth of quaternary III-nitride compounds by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2003, 82, 2242-2244.	3.3	31
90	Electrooptical Modulator at Telecommunication Wavelengths Based on GaNâ€"AlN Coupled Quantum Wells. IEEE Photonics Technology Letters, 2008, 20, 724-726.	2.5	31

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91	Effect of Bias on the Response of GaN Axial pâ€“n Junction Single-Nanowire Photodetectors. Nano Letters, 2019, 19, 5506-5514.	9.1	31
92	Analysis of the Visible and UV Electroluminescence in Homojunction GaN LED's. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	30
93	Effects of stacking on the structural and optical properties of self-organized GaN/AlN quantum dots. Applied Physics Letters, 2004, 84, 4224-4226.	3.3	30
94	Ga kinetics in plasma-assisted molecular-beam epitaxy of GaN(112Â¯2): Effect on the structural and optical properties. Journal of Applied Physics, 2008, 103, .	2.5	30
95	Visible-blind ultraviolet photodetectors based on ZnMgBeSe Schottky barrier diodes. Applied Physics Letters, 2001, 78, 4190-4192.	3.3	29
96	High frequency (f=2.37â€…GHz) room temperature operation of 1.55â€…[micro sign]m AlNâˆ•GaN-based intersubband detector. Electronics Letters, 2007, 43, 185.	1.0	29
97	Strain relaxation in GaN/AlxGa1-xN superlattices grown by plasma-assisted molecular-beam epitaxy. Journal of Applied Physics, 2011, 110, .	2.5	29
98	Photodetectors based on intersubband transitions using III-nitride superlattice structures. Journal of Physics Condensed Matter, 2009, 21, 174208.	1.8	27
99	Indium kinetics during the plasma-assisted molecular beam epitaxy of semipolar (11âˆ’22) InGaN layers. Applied Physics Letters, 2010, 96, 181907.	3.3	27
100	Nonlinear absorption of InN/InGaN multiple-quantum-well structures at optical telecommunication wavelengths. Applied Physics Letters, 2011, 98, .	3.3	27
101	Terahertz absorbing AlGaN/GaN multi-quantum-wells: Demonstration of a robust 4-layer design. Applied Physics Letters, 2013, 103, 091108.	3.3	27
102	Correlation of optical and structural properties of GaN/AlN multi-quantum wellsâ€”<i>Ab initio</i> and experimental study. Journal of Applied Physics, 2016, 119, 015703.	2.5	27
103	Effects of Bias on the Responsivity of GaN Metalâ€“Semiconductorâ€“Metal Photodiodes. Physica Status Solidi A, 1999, 176, 157-161.	1.7	26
104	Submicron technology for III-nitride semiconductors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 2071.	1.6	26
105	Nonpolar<i>m</i>-plane GaN/AlGaN heterostructures with intersubband transitions in the 5â€“10 THz band. Nanotechnology, 2015, 26, 435201.	2.6	26
106	Intersubband transitions in nonpolar GaN/Al(Ga)N heterostructures in the short- and mid-wavelength infrared regions. Journal of Applied Physics, 2015, 118, 014309.	2.5	26
107	Optical and morphological properties ofGaNquantum dots doped withTm. Physical Review B, 2005, 71, .	3.2	25
108	Pseudo-square AlGaN/GaN quantum wells for terahertz absorption. Applied Physics Letters, 2014, 105, 131106.	3.3	25

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109	Surfactant effect of gallium during the growth of GaN on AlN(0001Â¯) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2004, 85, 1421-1423.	3.3	24
110	Dependence of the photovoltaic performance of pseudomorphic InGaN/GaN multiple-quantum-well solar cells on the active region thickness. Applied Physics Letters, 2016, 108, .	3.3	24
111	Effect of doping on the intersubband absorption in Si- and Ge-doped GaN/AlN heterostructures. Nanotechnology, 2017, 28, 405204.	2.6	24
112	Nanowire photodetectors based on wurtzite semiconductor heterostructures. Semiconductor Science and Technology, 2019, 34, 053002.	2.0	24
113	AlGaN Photodiodes For Monitoring Solar UV Radiation. Journal of Geophysical Research, 2000, 105, 4865-4871.	3.3	23
114	Intraband emission at Î»â‰ˆ1.48Î¼m from GaNâˆ•AlN quantum dots at room temperature. Applied Physics Letters, 2008, 92, 161105.	3.3	23
115	<i>Ab initio</i> and experimental studies of polarization and polarization related fields in nitrides and nitride structures. AIP Advances, 2017, 7, .	1.3	23
116	Ultra-low threshold polariton lasing at room temperature in a GaN membrane microcavity with a zero-dimensional trap. Scientific Reports, 2017, 7, 5542.	3.3	23
117	High UV/visible contrast photodiodes based on epitaxial lateral overgrown GaN layers. Electronics Letters, 1999, 35, 1488.	1.0	22
118	Application and Performance of GaN Based UV Detectors. Physica Status Solidi A, 2001, 185, 91-97.	1.7	22
119	Investigation of metalâ€“GaN and metalâ€“AlGaN contacts by XPS depth profiles and by electrical measurements. Journal of Crystal Growth, 2001, 230, 558-563.	1.5	22
120	Morphological properties of GaN quantum dots doped with Eu. Applied Physics Letters, 2004, 84, 2247-2249.	3.3	22
121	Room-temperature intersubband emission of GaN/AlN quantum wells at =2.3â€…[micro sign]m. Electronics Letters, 2006, 42, 1308.	1.0	22
122	Third order nonlinear susceptibility of InN at near band-gap wavelengths. Applied Physics Letters, 2007, 90, 091903.	3.3	22
123	Thermal stability of the deep ultraviolet emission from AlGaN/AlN Stranski-Krastanov quantum dots. Applied Physics Letters, 2012, 101, .	3.3	22
124	Systematic study of near-infrared intersubband absorption of polar and semipolar GaN/AlN quantum wells. Journal of Applied Physics, 2013, 113, .	2.5	22
125	Photovoltaic Response of InGaN/GaN Multiple-Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2013, 52, 08JH05.	1.5	22
126	Impact of recess etching and surface treatments on ohmic contacts regrown by molecular-beam epitaxy for AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2016, 109, .	3.3	22

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127	Electrical and optical properties of heavily Ge-doped AlGaN. Journal Physics D: Applied Physics, 2019, 52, 125101.	2.8	22
128	High detectivity ZnSe-based Schottky barrier photodetectors for blue and near-ultraviolet spectral range. Electronics Letters, 2000, 36, 826.	1.0	21
129	Resonant Raman scattering in self-assembledGaNâˆ•AlNquantum dots. Physical Review B, 2006, 74, .	3.2	21
130	Defect structure in heteroepitaxial semipolar (11ar {2} 2) (Ga, Al)N. Journal of Physics Condensed Matter, 2010, 22, 355802.	1.8	21
131	Environmental sensitivity of <i>n-i-n</i> and undoped single GaN nanowire photodetectors. Applied Physics Letters, 2013, 102, .	3.3	21
132	AlGaN photodetectors grown on Si(111) by molecular beam epitaxy. Journal of Crystal Growth, 2001, 230, 544-548.	1.5	20
133	GaN quantum dots doped with Tb. Applied Physics Letters, 2006, 88, 053102.	3.3	20
134	Mg doping and its effect on the semipolar GaN(112Â¯2) growth kinetics. Applied Physics Letters, 2009, 95, 171908.	3.3	20
135	Morphology and strain of self-assembled semipolar GaN quantum dots in (112Â¯2) AlN. Journal of Applied Physics, 2010, 108, .	2.5	20
136	Strong suppression of internal electric field in GaN/AlGaN multi-layer quantum dots in nanowires. Applied Physics Letters, 2011, 99, .	3.3	20
137	Carrier localization in InN/InGaN multiple-quantum wells with high In-content. Applied Physics Letters, 2012, 101, 062109.	3.3	20
138	Low-noise metal-insulator-semiconductor UV photodiodes based on GaN. Electronics Letters, 2000, 36, 2096.	1.0	19
139	Recent progresses of the BOLD investigation towards UV detectors for the ESA Solar Orbiter. Diamond and Related Materials, 2002, 11, 427-432.	3.9	19
140	Eu locations in Eu-doped InGaNâˆ•GaN quantum dots. Applied Physics Letters, 2005, 87, 021906.	3.3	19
141	Improved luminescence and thermal stability of semipolar (11-22) InGaN quantum dots. Applied Physics Letters, 2011, 98, 201911.	3.3	19
142	Effect of the barrier thickness on the performance of multiple-quantum-well InGaN photovoltaic cells. Japanese Journal of Applied Physics, 2015, 54, 072302.	1.5	19
143	Schottky Barrier Ultraviolet Photodetectors on Epitaxial Lateral Overgrown GaN. Physica Status Solidi A, 1999, 176, 141-145.	1.7	18
144	Deep levels in MOCVD n-type hexagonal gallium nitride studied by high resolution deep level transient spectroscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 91-94.	3.5	18

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145	Reliability of Schottky Contacts on AlGaN. Physica Status Solidi A, 2001, 188, 367-370.	1.7	18
146	Polytype transition of N-face GaN:Mg from wurtzite to zinc-blende. Journal of Applied Physics, 2004, 96, 3709-3715.	2.5	18
147	Ultrafast relaxation and optical saturation of intraband absorption of GaN/AlN quantum dots. Applied Physics Letters, 2009, 94, .	3.3	18
148	Improved conversion efficiency of as-grown InGaN/GaN quantum-well solar cells for hybrid integration. Applied Physics Express, 2014, 7, 032301.	2.4	18
149	Ultraviolet Photodetectors Based on Al_xGa_{1-x}N Schottky Barriers. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	17
150	Biâ€stable behaviour in GaNâ€based resonant tunnelling diode structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 431-434.	0.8	17
151	GaN quantum dots as optical transducers for chemical sensors. Applied Physics Letters, 2009, 94, 113108.	3.3	17
152	Resonant Tunneling Transport in a GaN/AlN Multiple-Quantum-Well Structure. Applied Physics Express, 2012, 5, 052203.	2.4	17
153	Two-step method for the deposition of AlN by radio frequency sputtering. Thin Solid Films, 2013, 545, 149-153.	1.8	17
154	Long-lived excitons in GaN/AlN nanowire heterostructures. Physical Review B, 2015, 91, .	3.2	17
155	Composition Analysis of III-Nitrides at the Nanometer Scale: Comparison of Energy Dispersive X-ray Spectroscopy and Atom Probe Tomography. Nanoscale Research Letters, 2016, 11, 461.	5.7	17
156	Characterization of the Resonant Third-Order Nonlinear Susceptibility of Si-Doped GaNâ€“AlN Quantum Wells and Quantum Dots at 1.5 mum. IEEE Photonics Technology Letters, 2008, 20, 1366-1368.	2.5	16
157	High frequency measurements on an AlNâˆ•GaN-based intersubband detector at 1550 and 780nm. Applied Physics Letters, 2008, 92, 231104.	3.3	16
158	GaN-based quantum cascade photodetector with 1.5â€…[micro sign]m peak detection wavelength. Electronics Letters, 2010, 46, 1685.	1.0	16
159	Improvement of InN layers deposited on Si(111) by RF sputtering using a low-growth-rate InN buffer layer. Thin Solid Films, 2012, 520, 2805-2809.	1.8	16
160	Waveguide saturable absorbers at 155 Î¼m based on intraband transitions in GaN/AlN QDs. Optics Express, 2013, 21, 27578.	3.4	16
161	Study of high In-content AlInN deposition on p-Si(111) by RF-sputtering. Japanese Journal of Applied Physics, 2016, 55, 05FB07.	1.5	16
162	Effect of doping on the far-infrared intersubband transitions in nonpolar<i>m</i>-plane GaN/AlGaN heterostructures. Nanotechnology, 2016, 27, 145201.	2.6	16

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163	Design of polarization-insensitive superconducting single photon detectors with high-index dielectrics. Superconductor Science and Technology, 2017, 30, 035005.	3.5	16
164	Intersubband absorption in Siâ€•and Geâ€doped GaN/AlN heterostructures in selfâ€assembled nanowire and 2D layers. Physica Status Solidi (B): Basic Research, 2017, 254, 1600734.	1.5	16
165	Switching of exciton character in double InGaN/GaN quantum wells. Physical Review B, 2018, 98, .	3.2	16
166	UV Emission from GaN Wires with <i>m</i>-Plane Coreâ€"Shell GaN/AlGaN Multiple Quantum Wells. ACS Applied Materials & Interfaces, 2020, 12, 44007-44016.	8.0	16
167	Raman study and theoretical calculations of strain in GaN quantum dot multilayers. Physical Review B, 2006, 73, .	3.2	15
168	Monolithically integrated AlGaN/GaN/AlN-based solar-blind ultraviolet and near-infrared detectors. Electronics Letters, 2008, 44, 986.	1.0	15
169	Stranskiâ€"Krastanow growth of (112Â¯2)-oriented GaN/AlN quantum dots. Applied Physics Letters, 2009, 94, 111901.	3.3	15
170	In-rich Al_{<i>x</i>}In_{1â^'<i>x</i>}N grown by RF-sputtering on sapphire: from closely-packed columnar to high-surface quality compact layers. Journal Physics D: Applied Physics, 2017, 50, 065101.	2.8	15
171	Effect of the nanowire diameter on the linearity of the response of GaN-based heterostructured nanowire photodetectors. Nanotechnology, 2018, 29, 255204.	2.6	15
172	Quality improvement of AlInN/p-Si heterojunctions with AlN buffer layer deposited by RF-sputtering. Journal of Alloys and Compounds, 2018, 769, 824-830.	5.5	15
173	Study of high quality AlN layers grown on Si(111) substrates by plasma-assisted molecular beam epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	14
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